# 2.5V Drive Nch MOS FET RTR025N03

#### Structure

Silicon N-channel MOS FET

### ● Features

- 1) Low On-resistance.
- 2) Space saving-small surface mount package (TSMT3).
- 3) Low voltage drive (2.5V drive).

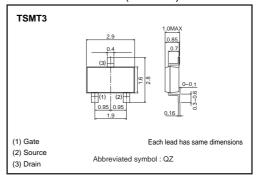
# Applications

Switching

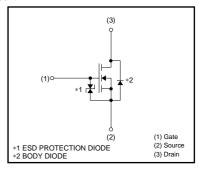
## ●Packaging specifications and hfe

	Package	Taping	
Type	Code	TL	
	Basic ordering unit (pieces)	3000	
RTR025N03		0	

# ●External dimensions (Unit : mm)



#### •Inner circuit



# ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		$V_{DSS}$	30	V	
Gate-source voltage		V <sub>GSS</sub>	12	V	
Dunin assument	Continuous	I <sub>D</sub>	±2.5	Α	
Drain current	Pulsed	I <sub>DP</sub> *1	±10	Α	
Source current	Continuous	Is	0.8	Α	
(Body diode)	Pulsed	I <sub>SP</sub> *1	10	Α	
Total power dissipation		P <sub>D</sub> *2	1.0	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W

<sup>\*</sup> Mounted on a ceramic board

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	1	-	10	μΑ	Vgs=12V, Vps=0V
Drain-source breakdown voltage	$V_{(BR)\;DSS}$	30	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.5	_	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance		-	66	92	mΩ	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 4.5V
	R <sub>DS (on)</sub> *	-	70	98	mΩ	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 4V
		-	95	133	mΩ	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub>   *	2.0	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.5A
Input capacitance	Ciss	-	220	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	60	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	35	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	9	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	_	15	_	ns	ID= 1.25A
Turn-off delay time	td (off) *	_	25	_	ns	V <sub>GS</sub> = 4.5V R <sub>L</sub> =12Ω
Fall time	t <sub>f</sub> *	-	10	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	3.3	4.6	nC	V <sub>DD</sub> ≒15V V <sub>GS</sub> =4.5V
Gate-source charge	Q <sub>gs</sub> *	_	0.7	_	nC	ID= 2.5A
Gate-drain charge	Q <sub>gd</sub> *	_	1.0	-	nC	RL=6Ω R <sub>G</sub> =10Ω

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	-	-	1.2	V	I <sub>S</sub> = 0.8A, V <sub>GS</sub> =0V

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